

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	317	"end point" same etch\$4 same wavelength	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:50
L3	413	(SiN or "silicon nitride") same (ARC or BARC) same etch\$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:38
L4	22	3 and "end point"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:46
L5	69	(SiN or "silicon nitride") and (ARC or BARC or "anti reflective") and etch\$4 and "end point" and wavelength	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:44
L6	123	(SiN or "silicon nitride") and (ARC or BARC or "anti reflective") and etch\$4 and "end point" and plasma	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:45
L7	2743	(SiN or "silicon nitride") and (ARC or BARC or "anti reflective") and etch\$4 and (plasma or "dry etch")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:49
L9	1195	7 and (emission or wavelength)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:48
L10	319	9 and (chlorine or "Cl.sub.2") and (oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 08:31
L11	93	1 and (SiN or "silicon nitride" or ARC or BARC or "anti reflective")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:50
L12	741	"end point" and etch\$4 and wavelength and (plasma or "dry etch")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/28 07:51